LISTING OF CLAIMS:

1. (CURRENTLY AMENDED) A method for manufacturing MTJ cell of magnetic random access memory (MRAM) comprising:

forming a stacked structure of a pinned magnetic layer, an alumina layer and a free magnetic layer;

forming a hard mask layer on the stacked structure;

patterning the hard mask layer via a photoetching process using a MTJ cell mask to form a hard mask layer pattern exposing a portion of the free magnetic layer;

subjecting the exposed portion of the free magnetic layer to a halo ion implant process to convert the state of the exposed portion into an amorphous state;

oxidizing the exposed portion of the free magnetic layer in the amorphous state; and

patterning a MTJ cell by etching the stacked structure.

2. (ORIGINAL) The method according to claim 1, wherein the halo ion implant process is performed in a manner that a tilt angle ranges from 0 to 90 and [[a]] an ion is implanted from four directions.